Abstracts

Tunable Far-Infrared Source-Detector System Based on Landau-Level Transitions in n-InSb

E. Gornik, W. Muller and F. Kohl. "Tunable Far-Infrared Source-Detector System Based on Landau-Level Transitions in n-InSb." 1974 Transactions on Microwave Theory and Techniques 22.12 (Dec. 1974, Part I [T-MTT] (Special Issue on the Proceedings of the First International Conference on Submillimeter Waves and Their Applications)): 991-995.

The radiative emission from impact-ionized shallow donors in n-type InSb provides a tunable far-infrared source, the properties and applications of which are investigated. To obtain optimum conditions, the radiation intensity is studied independence of the sample volume and the electric- and magnetic-field intensities. The source is applied to measure the Zeeman splitting of the shallow donors in n-InP and n-GaAs.

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